

1x4 25Gb/s Photodiode Chip

CPC0003C

Features

- Top illuminated InGaAs/InP p-i-n PD 1x4 array
- Coplanar GSG contact pads
- Low cost and High reliability

Applications

- Receiver for 100GbE and OTU4
- Datacom and Telecom up to 28Gb/s

Absolute Maximum Ratings

Parameters	Symbol	Rating	Unit
Reverse voltage	V_R	20	V
Reverse Current	I_R	2	mA
Forward current	I_F	10	mA
Optical input power	P_{max}	5	dBm
Operating temperature range	T_C	-40 to +85	°C
Storage temperature range	T_{STG}	-40 to +125	°C

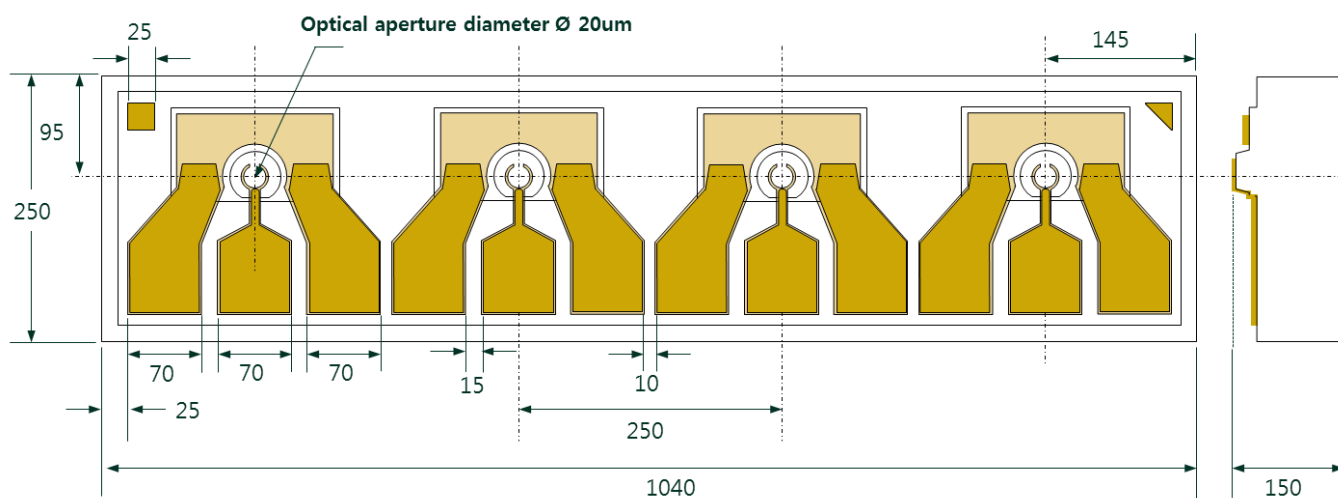
Electro-Optical Characteristics (Typical values are at 25 °C)

Parameters	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Operating wavelength range	λ	-	1100	-	1640	nm
Responsivity*	R	1310nm, $V_R=2.5V$	0.7	0.8	-	A/W
Dark current	I_D	$V_R=5V$	-	1	10	nA
Total capacitance	C	f=1MHz, $V_R=2.5V$	-	0.11	0.15	pF
OE bandwidth	BW	-3dB electrical	18	22	-	GHz

* depend on optical coupling efficiency

Dimensions

Parameters	Symbol	Test Condition	Unit
Optical aperture diameter	D	20	μm
Chip array dimension	W x H	1,040 x 250	μm^2
Chip thickness	T	150±20	μm
Photodiode pitch	-	250	μm
Bonding pad diameter	-	70	μm

(unit: μm)**Precaution to use**

The CPC0003C is sensitive to electrostatic discharge (ESD) and should be handled with appropriate caution. Please use standard ESD protective equipment when handling this product.

Ordering information

CPC0003C

Specifications described here are subject to change without notice



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